

# FX6KMJ-3

High-Speed Switching Use Pch Power MOS FET

REJ03G0263-0100 Rev.1.00 Aug.20.2004

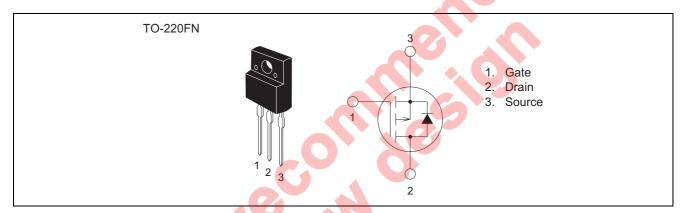
#### **Features**

 $\begin{array}{ll} \bullet & Drive\ voltage: 4\ V \\ \bullet & V_{DSS}: -150\ V \\ \bullet & r_{DS(ON)\ (max)}: 0.53\ \Omega \end{array}$ 

•  $I_D:-6A$ 

• Recovery Time of the Integrated Fast Recovery Diode (TYP.): 100 ns

#### **Outline**



### **Applications**

Motor control, lamp control, solenoid control, DC-DC converters, etc.

# **Maximum Ratings**

 $(Tc = 25^{\circ}C)$ 

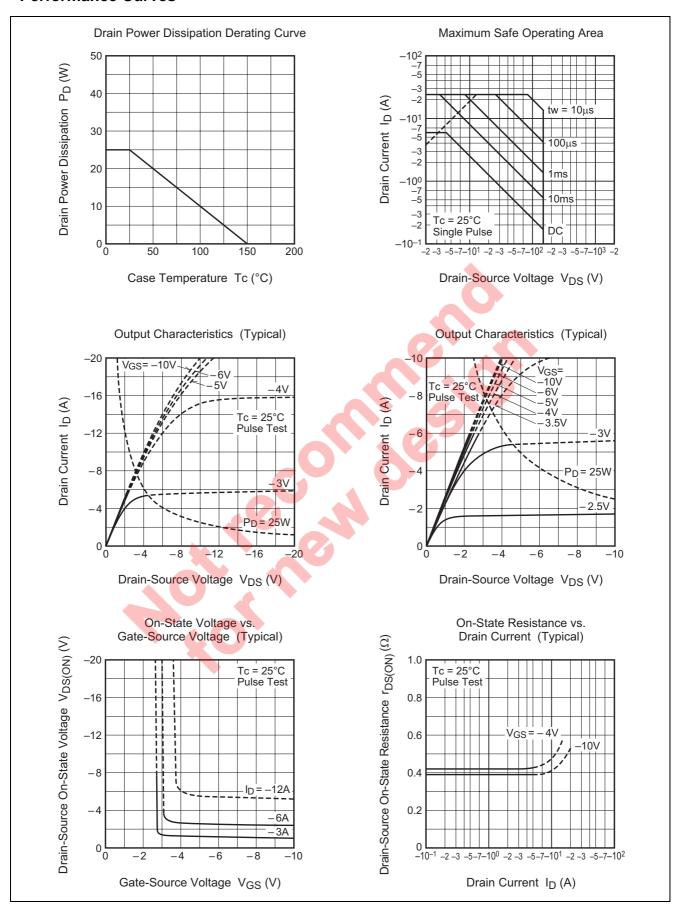
Parameter	Symbol	Ratings	Unit	Conditions
Drain-source voltage	V <sub>DSS</sub>	-150	V	V <sub>GS</sub> = 0 V
Gate-source voltage	V <sub>GSS</sub>	±20	V	V <sub>DS</sub> = 0 V
Drain current	I <sub>D</sub>	-6	А	
Drain current (Pulsed)	I <sub>DM</sub>	-24	Α	
Avalanche current (Pulsed)	I <sub>DA</sub>	-6	Α	L = 100 μH
Source current	Is	-6	Α	
Source current (Pulsed)	I <sub>SM</sub>	-24	Α	
Maximum power dissipation	P <sub>D</sub>	25	W	
Channel temperature	Tch	- 55 to +150	°C	
Storage temperature	Tstg	- 55 to +150	°C	
Isolation voltage	Viso	2000	V	AC 1 minute,
				Terminal to case
Mass	_	2.0	g	Typical value

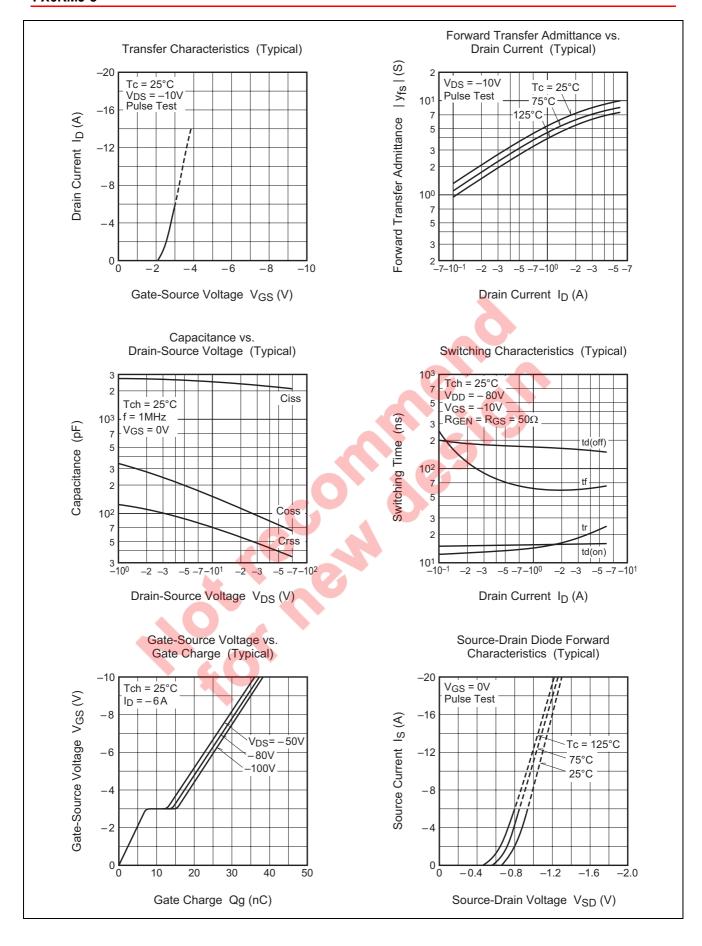
# **Electrical Characteristics**

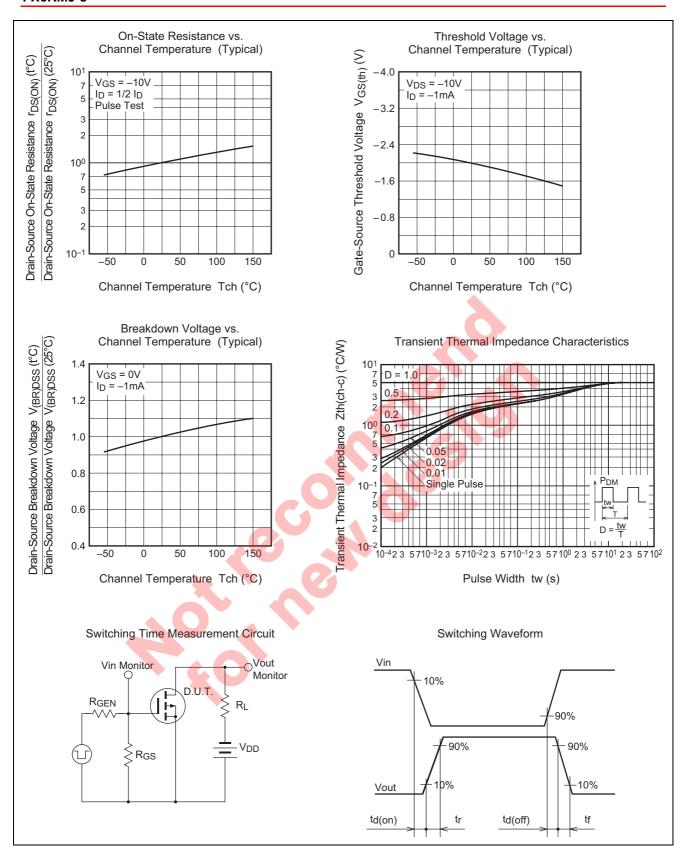
 $(Tch = 25^{\circ}C)$ 

Parameter	Symbol	Min.	Тур.	Max.	Unit	Test conditions	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	-150	_	_	V	$I_D = -1 \text{ mA}, V_{GS} = 0 \text{ V}$	
Gate-source leakage current	I <sub>GSS</sub>	_	_	±0.1	μΑ		
Drain-source leakage current	I <sub>DSS</sub>	_	_	-0.1	mA		
Gate-source threshold voltage	V <sub>GS(th)</sub>	-1.0	-1.5	-2.0	V	Test conditions $I_D = -1 \text{ mA, } V_{GS} = 0 \text{ V}$ $V_{GS} = \pm 20 \text{ V, } V_{DS} = 0 \text{ V}$ $V_{DS} = -150 \text{ V, } V_{GS} = 0 \text{ V}$ $I_D = -1 \text{ mA, } V_{DS} = -10 \text{ V}$ $I_D = -3 \text{ A, } V_{GS} = -10 \text{ V}$ $I_D = -3 \text{ A, } V_{GS} = -4 \text{ V}$ $I_D = -3 \text{ A, } V_{DS} = -10 \text{ V}$ $I_D = -3 \text{ A, } V_{DS} = -10 \text{ V}$ $V_{DS} = -10 \text{ V, } V_{GS} = 0 \text{ V, } f = 1 \text{ MHz}$ $V_{DD} = -80 \text{ V, } I_D = -3 \text{ A, } V_{GS} = -10 \text{ V}$ $R_{GEN} = R_{GS} = 50  \Omega$ $I_S = -3 \text{ A, } V_{GS} = 0 \text{ V}$ $Channel \text{ to case}$ $I_S = -6 \text{ A, } dis/dt = 100 \text{ A/μs}$	
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.41	0.53	Ω	$I_D = -3 \text{ A}, V_{GS} = -10 \text{ V}$	
Drain-source on-state resistance	r <sub>DS(ON)</sub>	_	0.45	0.59	Ω	$I_D = -3 \text{ A}, V_{GS} = -4 \text{ V}$	
Drain-source on-state voltage	V <sub>DS(ON)</sub>	_	-1.23	-1.59	V		
Forward transfer admittance	y <sub>fs</sub>	_	7.9	_	S	$I_D = -3 \text{ A}, V_{DS} = -10 \text{ V}$	
Input capacitance	Ciss	_	2420	_	pF		
Output capacitance	Coss	_	152	_	pF		
Reverse transfer capacitance	Crss	_	69	_	pF		
Turn-on delay time	t <sub>d(on)</sub>	_	14	_	ns	$V_{DD} = -80 \text{ V}, I_D = -3 \text{ A},$	
Rise time	t <sub>r</sub>	_	18	_	ns	$V_{GS} = -10 \text{ V},$	
Turn-off delay time	t <sub>d(off)</sub>	_	156	_	ns		
Fall time	t <sub>f</sub>	_	58		ns		
Source-drain voltage	$V_{SD}$	_	-1.0	-1.5	V	$I_S = -3 \text{ A}, V_{GS} = 0 \text{ V}$	
Thermal resistance	Rth(ch-c)	_	_	5.00	°C/W	Channel to case	
Reverse recovery time	t <sub>rr</sub>	_	100		ns	$I_S = -6 \text{ A}, \text{ dis/dt} = 100 \text{ A/}\mu\text{s}$	
				0,			

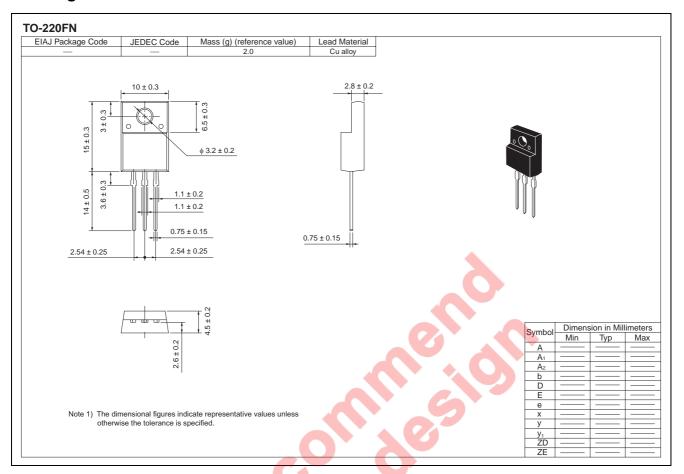
#### **Performance Curves**







# **Package Dimensions**



# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Plastic Magazine (Tube)	50	Type name	FX6KMJ-3
Lead form	Plastic Magazine (Tube)	50	Type name – Lead forming code	FX6KMJ-3-A8

Note: Please confirm the specification about the shipping in detail.

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